

SiC Schottky Barrier Diode

V_R	650V
I _F	15A
Q_C	23nC

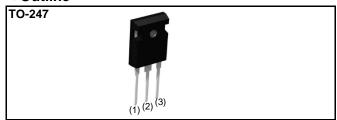
Features

- 1) Shorter recovery time
- 2) Reduced temperature dependence
- 3) High-speed switching possible

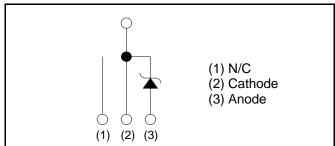
Construction

Silicon carbide epitaxial planer Shottoky Diode

Outline



•Inner circuit



Packaging specifications

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	Packaging	Tube		
	Reel size (mm)	-		
Type	Tape width (mm)	-		
Type	Basic ordering unit (pcs)	30		
	Packing code	С		
	Marking	SCS215AE		

●Absolute maximum ratings (T_i = 25°C)

Parameter	Symbol	Value	Unit	
Reverse voltage (repetitive peak)	V_{RM}	650	V	
Reverse voltage (DC)	V_R	650	V	
Continuous forward current	I _F	15* ¹	А	
		55* ²	А	
Surge no repetitive forward current	I _{FSM}	200* ³	А	
		43*4	А	
Repetitive peak forward current	I _{FRM}	61* ⁵	А	
Total power disspation	P _D	110* ⁶	W	
Junction temperature	T _j	175	°C	
Range of storage temperature	T _{stg}	-55 to +175	°C	

^{*1} T_c=130°C *2 PW=8.3ms sinusoidal, T_i=25°C *3 PW=10μs square, T_i=25°C

^{*4} PW=8.3ms sinusoidal, T_i=150°C *5 T_c=100°C, T_i=150°C, Duty cycle=10%

^{*6} T_c=25°C

●Electrical characteristics (T_j = 25°C)

Parameter	Symbol	Conditions	Values			Unit
raiailletei			Min.	Тур.	Max.	Offic
DC blocking voltage	V_{DC}	I _R =0.3mA	600	-	-	V
Forward voltage	V _F	I _F =15A,T _j =25°C	-	1.35	1.55	V
		I _F =15A,T _j =150°C	-	1.55	-	V
		I _F =15A,T _j =175°C	-	1.63	-	V
Reverse current	I _R	V _R =600V,T _j =25°C	-	3	300	μА
		V _R =600V,T _j =150°C	-	45	-	μА
		V _R =600V,T _j =175°C	-	105	-	μА
Total capacitance	С	V _R =1V,f=1MHz	-	550	-	pF
		V _R =600V,f=1MHz	-	56	-	pF
Total capacitive charge	Q_c	V _R =400V,di/dt=350A/μs	-	23	-	nC
Switching time	t _c	V _R =400V,di/dt=350A/μs	-	18	-	ns

●Thermal characteristics

Parameter	Symbol	Conditions	Values			Unit
			Min.	Тур.	Max.	Offic
Thermal resistance	$R_{\text{th(j-c)}}$	-	-	1.1	1.3	°C/W

•Electrical characteristic curves

Fig.1 V_F - I_F Characteristics

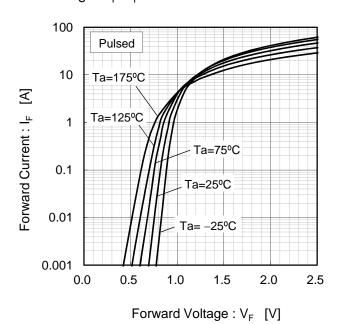
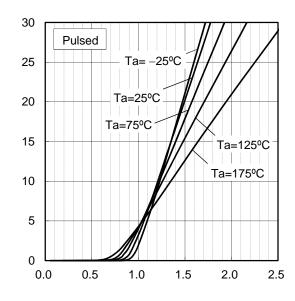


Fig.2 V_F - I_F Characteristics

Forward Current: I_F [A]



Forward Voltage : V_F [V]

Fig.3 V_R - I_R Characteristics

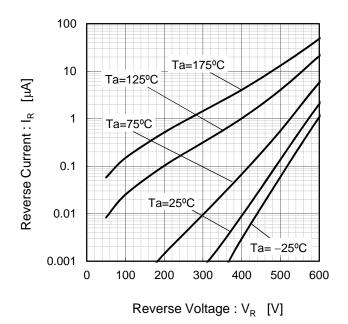
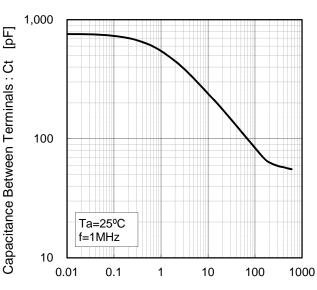


Fig.4 V_R-Ct Characteristics



Reverse Voltage : V_R [V]

•Electrical characteristic curves

Fig.5 Thermal Resistance vs. Pulse Width

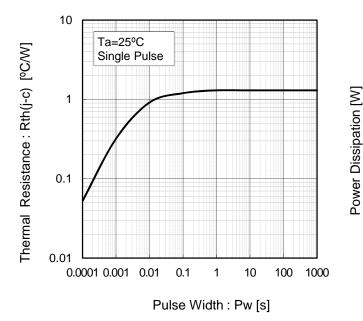
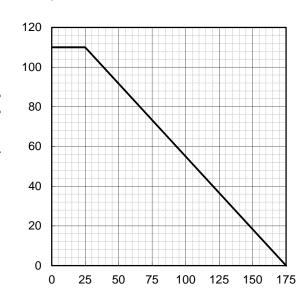


Fig.6 Power Dissipation



Case Temperature : Tc [°C]

Fig.7 Ip-Tc Derating Curve

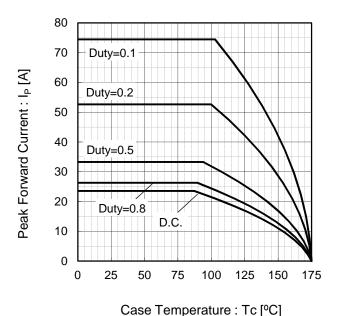
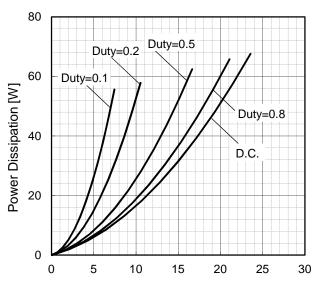


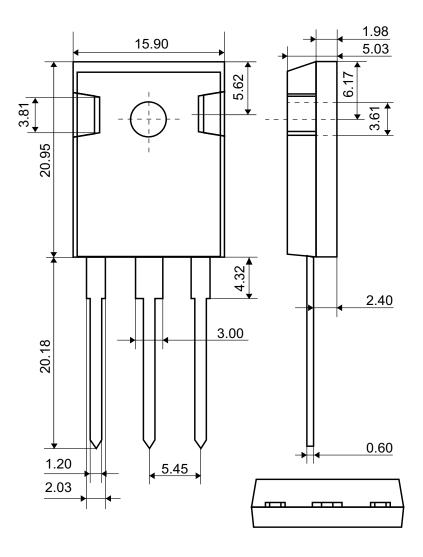
Fig.8 Io-Pf Characteristics



Average Rectified Forward Current: Io [A]

●Dimensions (Unit:mm)

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